

JC542 U.S. PTO

09/442499

11/18/99

et No. CS99-065

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Pr: PLASMA ETCH METHOD FOR FORMING PLASMA ETCHED SILICON LAYER

☒ 2 sheets of drawing(s) - formal.

☒ An assignment of the invention to **Chartered Semiconductor Manufacturing Ltd.**

☐ An associate power of attorney

FOR:	NO. FILED	NO. EXTRA	RATE	FEE
BASIC FEE				\$ 760.
TOTAL CLAIMS	16 -20=	0	x 18 =	\$ 0.
INDEP CLAIMS	3 -3=	0	x 78 =	\$ 0.
MULTIPLE DEPENDENT CLAIM PRESENTED			+ 260 =	
SUB TOTAL				\$ 760.
ASSIGNMENT				\$40.
TOTAL				\$ 800.

X	TOTAL	\$ 800.
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Please charge my Deposit Account No. 19-0033 in the amount of \$ 800. A duplicate copy of this sheet is enclosed.

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- ☒ Any additional filing fees required under 37 CFR \$1.16.
- ☒ Any patent application processing fees under 37 CFR \$1.17.

Respectfully submitted,
STEPHEN B. ACKERMAN, REG. NO. 37,761